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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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2SJ387(L), 2SJ387(S)

Silicon P-Channel MOS FET

RENESAS

ADE-208-1196 (Z)
1st. Edition
Mar. 2001

Application

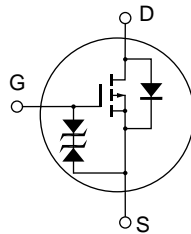
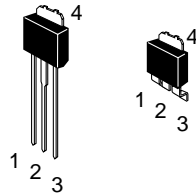
High speed power switching

Features

- Low on-resistance
- Low drive current
- 2.5 V Gate drive device can be driven from 3 V Source
- Suitable for Switching regulator, DC - DC converter

Outline

DPAK-2



1. Gate
2. Drain
3. Source
4. Drain

2SJ387(L), 2SJ387(S)

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	-20	V
Gate to source voltage	V _{GSS}	±10	V
Drain current	I _D	-10	A
Drain peak current	I _{D(pulse)} ^{*1}	-40	A
Body to drain diode reverse drain current	I _{DR}	-10	A
Channel dissipation	Pch ^{*2}	20	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

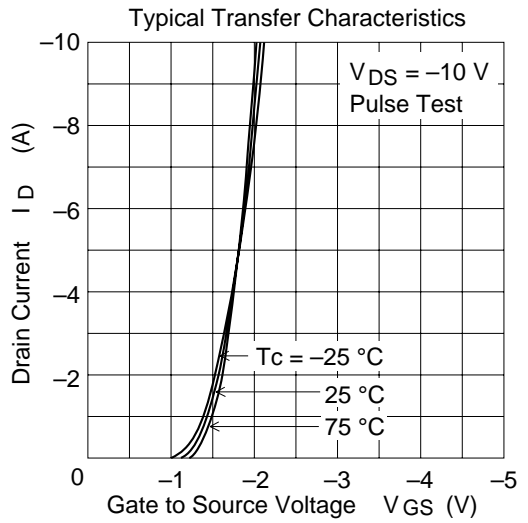
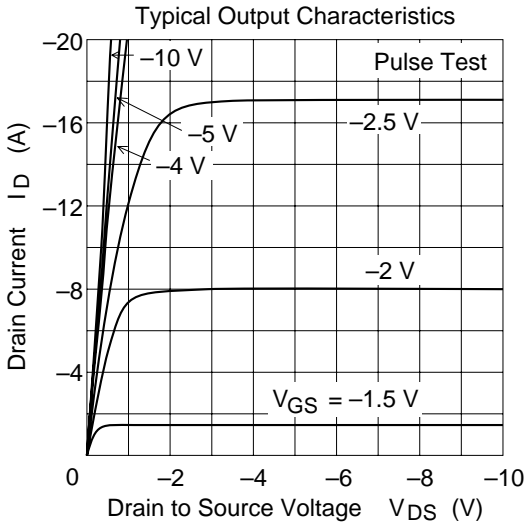
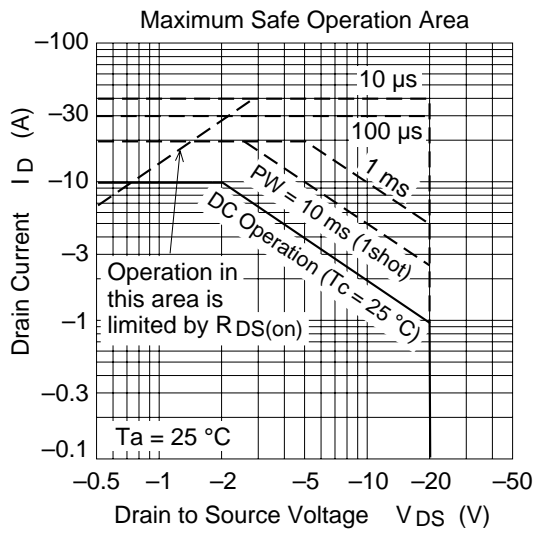
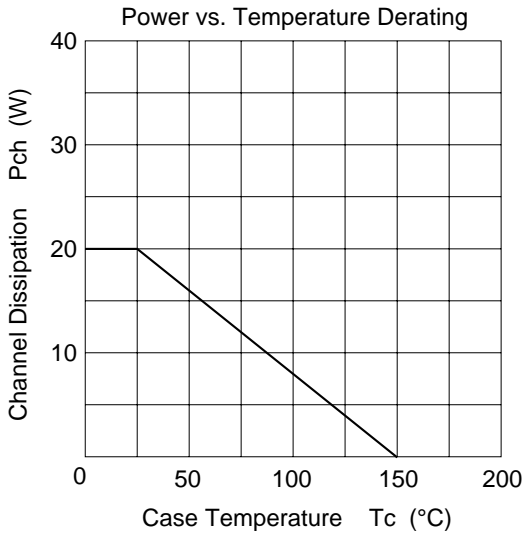
Notes: 1. PW ≤ 10 μs, duty cycle ≤ 1 %

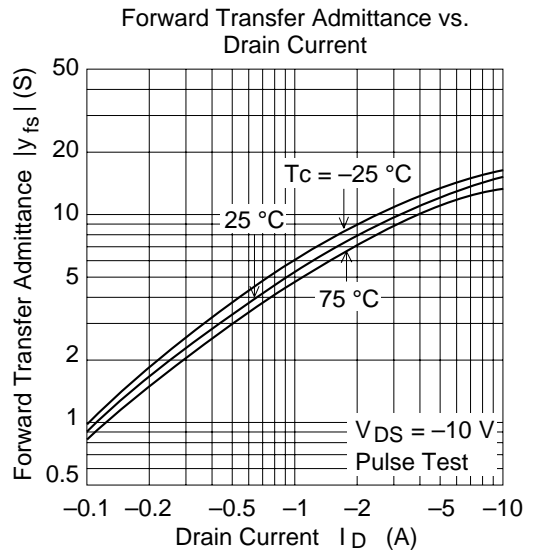
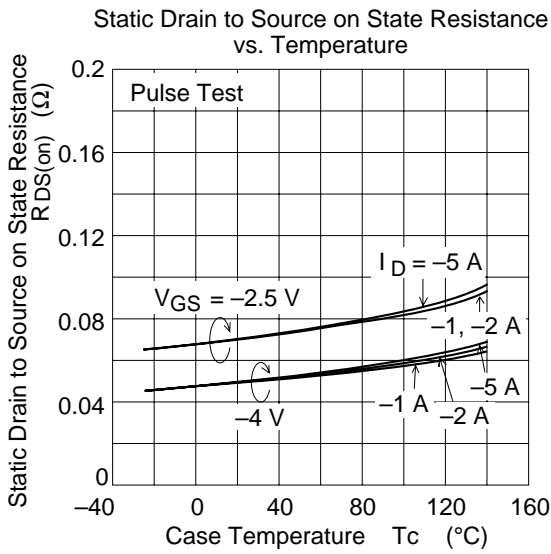
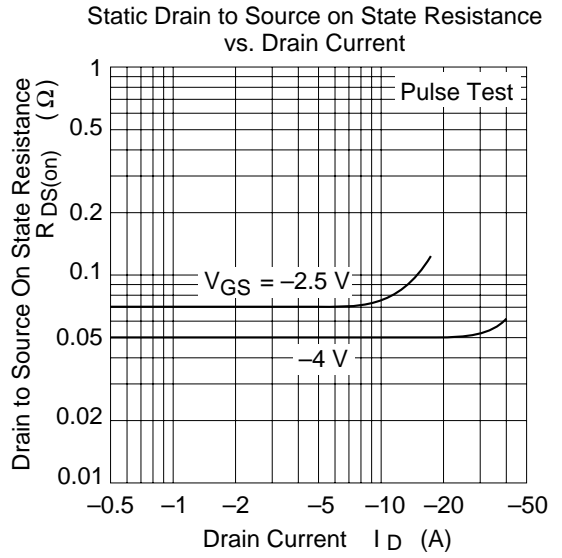
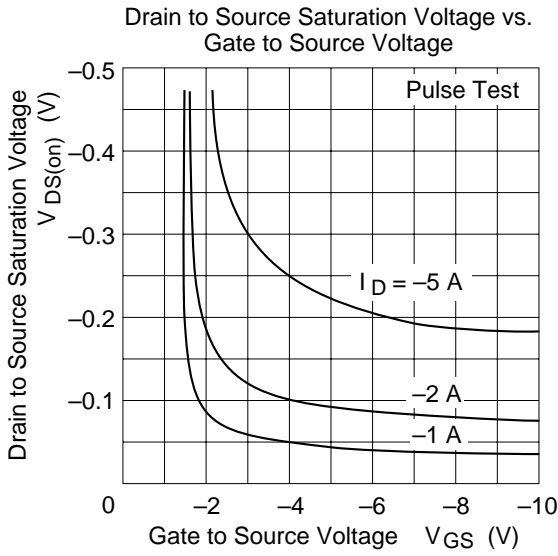
2. Value at Tc = 25°C

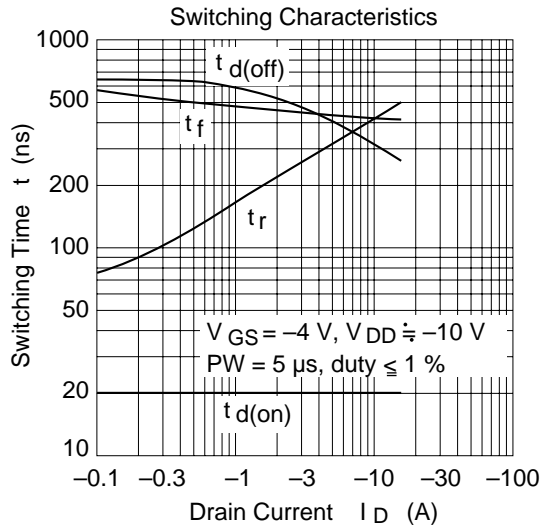
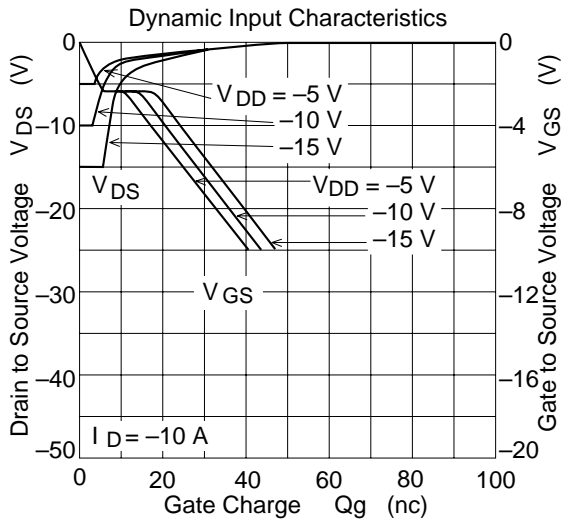
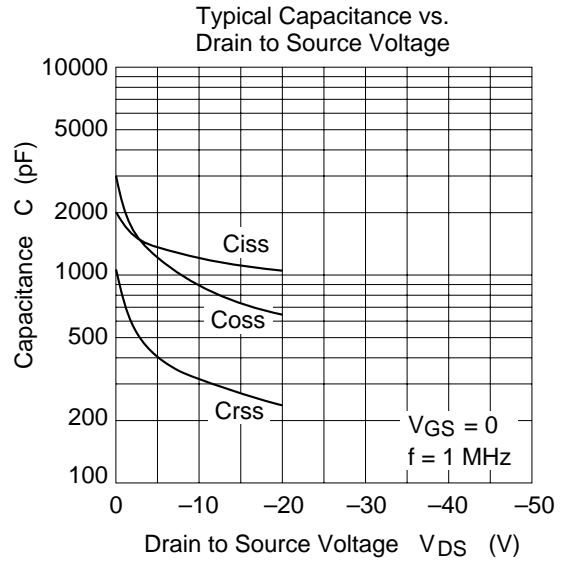
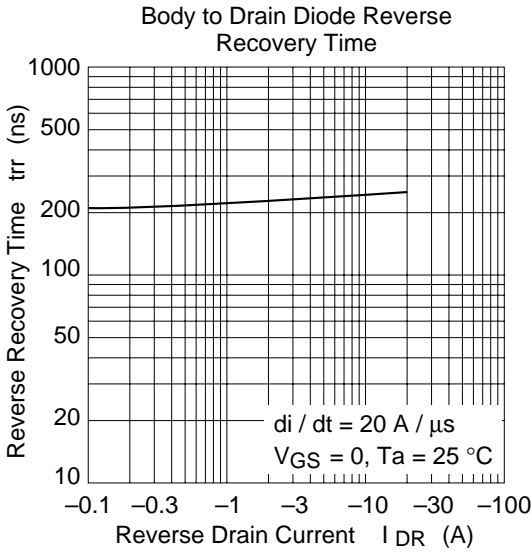
Electrical Characteristics (Ta = 25°C)

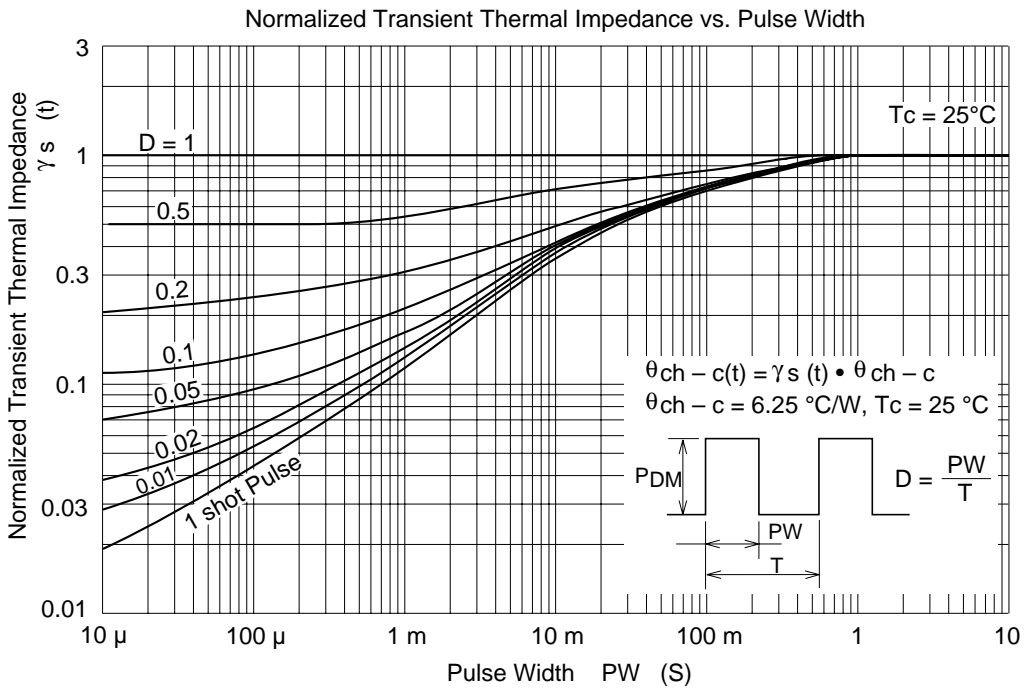
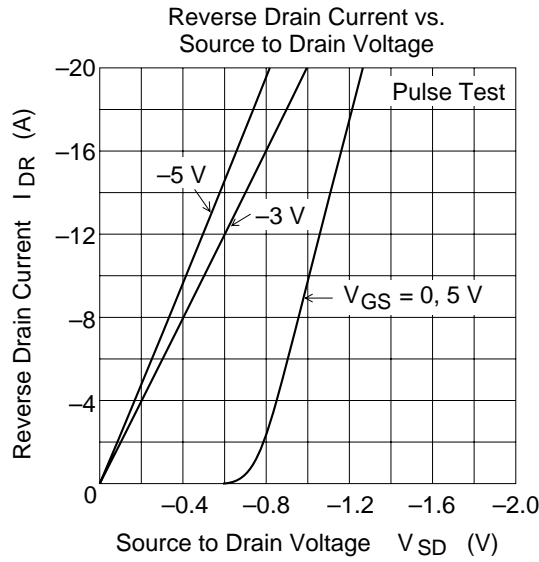
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	-20	—	—	V	$I_D = -10 \text{ mA}$, $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	± 10	—	—	V	$I_G = \pm 200 \mu\text{A}$, $V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 6.5 \text{ V}$, $V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	-100	μA	$V_{DS} = -16 \text{ V}$, $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	-0.5	—	-1.5	V	$I_D = -1 \text{ mA}$, $V_{DS} = -10 \text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.05	0.07	Ω	$I_D = -5 \text{ A}$ $V_{GS} = -4 \text{ V}^{*1}$
			—	0.07	0.1	Ω
Forward transfer admittance	$ y_{fs} $	7	12	—	S	$I_D = -5 \text{ A}$ $V_{DS} = -10 \text{ V}^{*1}$
Input capacitance	C_{iss}	—	1170	—	pF	$V_{DS} = -10 \text{ V}$
Output capacitance	C_{oss}	—	860	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	C_{rss}	—	310	—	pF	$f = 1 \text{ MHz}$
Turn-on delay time	$t_{d(on)}$	—	20	—	ns	$I_D = -5 \text{ A}$
Rise time	t_r	—	325	—	ns	$V_{GS} = -4 \text{ V}$
Turn-off delay time	$t_{d(off)}$	—	350	—	ns	$R_L = 2 \Omega$
Fall time	t_f	—	425	—	ns	
Body to drain diode forward voltage	V_{DF}	—	-1.0	—	V	$I_F = -10 \text{ A}$, $V_{GS} = 0$
Body to drain diode reverse recovery time	t_{rr}	—	240	—	ns	$I_F = -10 \text{ A}$, $V_{GS} = 0$, $diF/dt = 20 \text{ A}/\mu\text{s}$

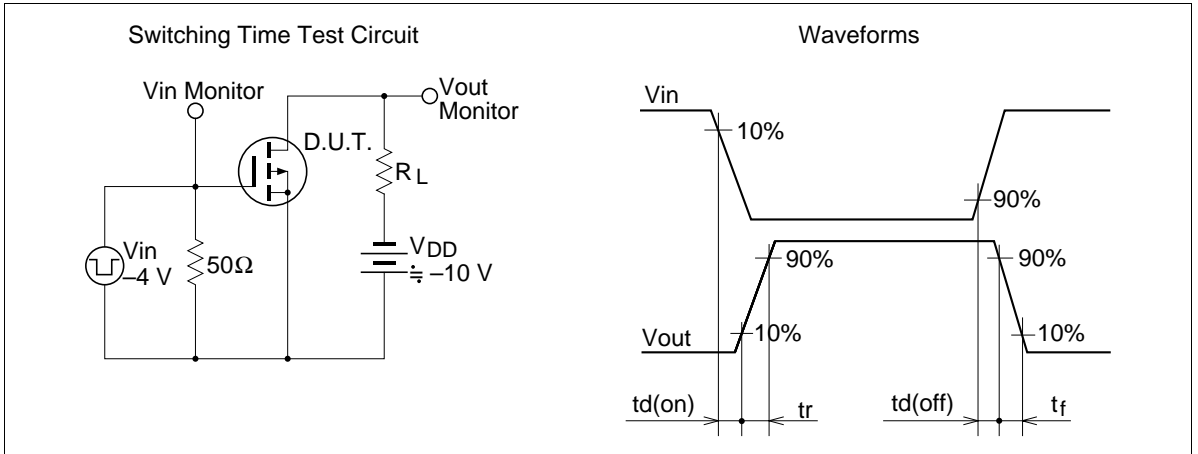
Note: 1. Pulse Test







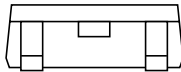
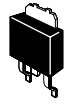
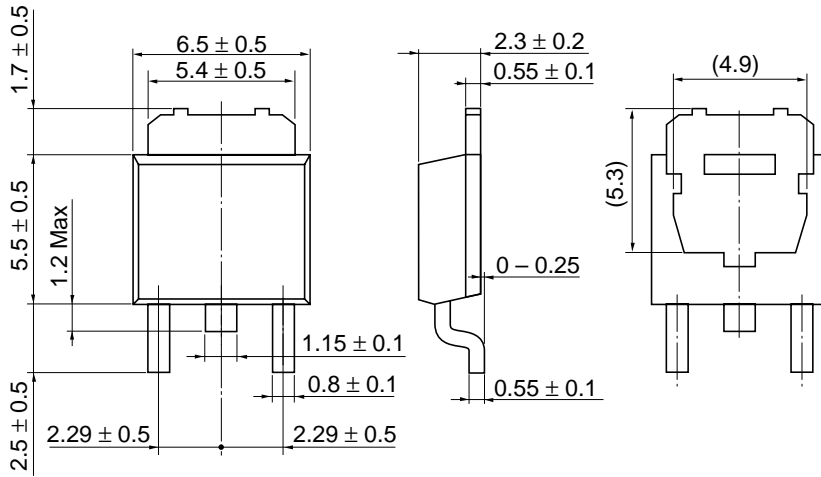




2SJ387(L), 2SJ387(S)

As of January, 2001

Unit: mm



Hitachi Code	DPAK (S)-(1),(2)
JEDEC	—
EIAJ	Conforms
Mass (reference value)	0.28 g

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HITACHI

Hitachi, Ltd.

Semiconductor & Integrated Circuits.

Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL NorthAmerica : <http://semiconductor.hitachi.com/>
 Europe : <http://www.hitachi-eu.com/hel/ecg>
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For further information write to:

Hitachi Semiconductor
(America) Inc.
179 East Tasman Drive,
San Jose, CA 95134
Tel: <1> (408) 433-1990
Fax: <1> (408) 433-0223

Hitachi Europe GmbH
Electronic Components Group
Dornacher Straße 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 585160

Hitachi Asia Ltd.
Hitachi Tower
16 Collyer Quay #20-00,
Singapore 049318
Tel : <65>-538-6533/538-8577
Fax : <65>-538-6933/538-3877
URL : <http://www.hitachi.com.sg>

Hitachi Asia Ltd.
(Taipei Branch Office)
4/F, No. 167, Tun Hwa North Road,
Hung-Kuo Building,
Taipei (105), Taiwan
Tel : <886>-(2)-2718-3666
Fax : <886>-(2)-2718-8180
Telex : 23222 HAS-TP
URL : <http://www.hitachi.com.tw>

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower,
World Finance Centre,
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon,
Hong Kong
Tel : <852>-(2)-735-9218
Fax : <852>-(2)-730-0281
URL : <http://www.hitachi.com.hk>

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